

Low Voltage, 0.7 Ω , Triple SPDT Analog Switch

DESCRIPTION

The DG2753 is a low voltage, low on-resistance, triple single-pole/double-throw (SPDT) monolithic CMOS analog switch. The device is designed for operation from 1.65 V to 4.3 V single supply. The device is 1.8 V logic compatible within the full operation voltage range to interface with low voltage DSP or MCU control logic. These traits make it ideal for one cell Li-ion battery direct power in portable applications.

The DG2753 fully guarantees operation when V+ is as low as 1.8 V. When powered from a 3 V power supply, it has a 0.9 Ω on-resistance, with 0.1 Ω R_{ON} matching between channels, and 0.2 Ω (Max) R_{ON} flatness.

Each switch conducts signals across power rails equally well in both directions when on, and blocks up to the power supply level when off. It offers 30 nS $T_{\rm on}$ and 10 nS $T_{\rm off}$. Breakbefore-make is guaranteed.

The DG2753 is built on Vishay Siliconix's low voltage process. An epitaxial layer prevents latchup.

It is available in QFN16 3 x 3 mm and TSSOP16 packages. As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with lead (Pb)-free device terminations. For analog switching products manufactured in QFN packages, the lead (Pb)-free "-E4" suffix is being used as a designator for nickel-palladium-gold. The TSSOP-16 package is offered in lead (Pb)-free with 100 % matte Tin terminations. The "-E3" suffix is the designator. Both the 100 % matte Tin and nickel-palladium gold device terminations meet all JEDEC standards for reflow and MSL ratings.

FEATURES

- Low Voltage Operation (1.65 to 4.3 V)
- Low On-Resistance r_{ON} : 0.9 Ω at 2.7 V
- Fast Switching: T_{ON} = 30 ns
- T_{OFF} = 10 ns
- QFN-16 (3 x 3) Package
- Latch-Up Current > 300 mA (JESD78)

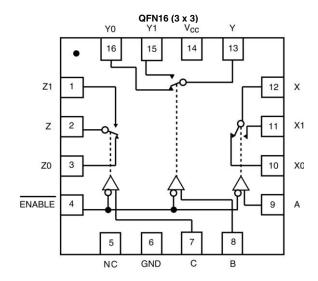
BENEFITS

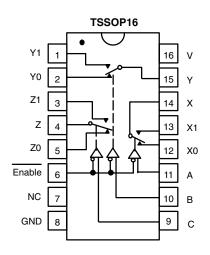
- Reduced Power Consumption
- · High Accuracy
- Reduce Board Space
- TTL/1.8 V Logic Compatible

APPLICATIONS

- Cellular Phones
- Speaker Headset Switching
- Audio and Video Signal Routing
- PCMCIA Cards
- · Battery Operated Systems

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





ORDERING INFORMATION					
Temp Range	Package	Part Number			
- 40 to 85 °C	TSSOP-16	DG2753DQ-T1-E3			
	16-Pin QFN (3 mm x 3 mm) Variation 2	DG2753DN-T1-E4			

Vishay Siliconix



TRUTH TABLE						
Enable Input		Select Inputs		ON Switches		
	С	В	Α	DG2753		
Н	Х	Х	Х	All switches open		
L	X	Х	L	X - X0		
L	Х	Х	Н	X - X1		
L	X	L	X	Y - Y0		
L	X	Н	X	Y - Y1		
L	L	Х	Х	Z- Z0		
L	Н	Х	X	Z - Z1		

X = Do not care

ABSOLUTE MAXIMUM RAT	INGS T _A = 25 °C, unless otherw	vise noted		
Parameter		Limit	Unit	
Defended to OND	V+	- 0.3 to 5.0	V	
Reference to GND	IN, COM, NC, NO ^a	- 0.3 to (V+ + 0.3)		
Current (Any terminal except NO, NC or COM)		30		
Continuous Current (NO, NC, or COM)		± 300	mA	
Peak Current (Pulsed at 1 ms, 10 % duty cycle)		± 500		
Storage Temperature (D Suffix)		- 65 to 150	°C	
Package Solder Reflow Conditions ^d	16-Pin QFN (3 x 3 mm)	250		
Power Dissipation (Packages) ^b QFN-16 ^c		1385	mW	

Notes:

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC Board.
- c. Derate 17.3 mW/°C above 70 °C.
- d. Manual soldering with iron is not recommended for leadless components. The QFN is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper lip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

SPECIFICATIONS							
	Symbol	Test Conditions Otherwise Unless Specified V+, ± 10 %, V _{IN} = 0.4 or 1.8 V ^e	Temp ^a	Limits - 40 to 85 °C			
Parameter				Min ^b	Typ ^c	Max ^b	Unit
Analog Switch						•	
Analog Signal Range ^d	V_{NO}, V_{NC}, V_{COM}		Full	0		V+	٧
On-Resistance	r _{DS(on)}	$V+ = 2.7 \text{ V}, I_{NO/NC} = 100 \text{ mA}, V_{COM} = 1.7 \text{ V}$	Room		0.9	1.3	Ω
		$V+ = 2.7 \text{ V}, I_{NO/NC} = 100 \text{ mA}, V_{COM} = 1.7 \text{ V}$	Full			1.5	
		V+ = 4.2 V, I _{NO/NC} = 100 mA, V _{COM} = 2.1 V	Room		0.7	1.2	
		V+ = 4.2 V, I _{NO/NC} = 100 mA, V _{COM} = 2.1 V	Full			1.4	
r _{ON} Match	$\Delta r_{(on)}$	$V+ = 2.7 \text{ V}, I_{NO/NC} = 100 \text{ mA}, V_{COM} = 1.7 \text{ V}$	Room			0.4	
		V+ = 4.3 V, I _{NO/NC} = 100 mA, V _{COM} = 2.1 V	Room			0.6	
r _{ON} Resistance Flatness	r _(on) Flatness	$V+ = 2.7 \text{ V}, I_{NO/NC} = 100 \text{ mA}, V_{COM} = 1.7 \text{ V}$	Room			0.2	
Switch Off Leakage Current	I _{NO(off)}	V+ = 4.3 V, V _{NO} , V _{NC} = 4 V/0.3 V,	Room Full	- 2 - 25		2 25	
	I _{COM(off)}	V _{COM} = 0.3 V/4 V	Room Full	- 2 - 25		2 25	nA
Channel-On Leakage Current	I _{COM(on)}	$V+ = 4.3 \text{ V}, V_{COM} = V_{NO}, V_{NC} = 0.3 \text{ V/4 V}$	Room Full	- 2 - 10		2 10	





SPECIFICATIONS								
		Test Conditions Otherwise Unless Specified		Limits - 40 to 85 °C				
Parameter	Symbol	V+, ± 10 %, V _{IN} = 0.4 or 1.8 V ^e	Temp ^a	Min ^b Typ ^c Max ^b			Unit	
Digital Control	Зуппоот	7 1, 2 10 75, 1 _{IN} 011 01 10 1	Temp	IVIIII	тур	IVIAA	Onit	
Input High Voltage	V _{INH}	V+ = 1.8 V	Full	1				
		V+ = 3 V	Full	1.4				
, , ,		V+ = 4.3 V	Full	1.8			.,	
		V+ = 1.8 V	Full			0.4	- V -	
Input Low Voltage	V_{INL}	V+ = 3 V	Full			0.5		
		V+ = 4.3 V	Full			0.5		
Input Current	I_{INL} , I_{INH}	$V_{IN} = 0 \text{ V or V} +$	Full	- 1		1	μΑ	
Dynamic Characteristics								
Turn-On Time	t _{ON}	$V_{+} = 2.7 \text{ V}$ $V_{NO}, V_{NC} = 1.5 \text{ V}, R_{L} = 50 \Omega, C_{L} = 35 \text{ pF}$	Room Full		30	60 65	ns	
Turn-Off Time	t _{OFF}		Room Full		10	30 40		
Break-Before-Make	t _{OPEN}	V+ = 2.7 V	Full	5	30			
Adress Transistion Time	t _{TRANS}	V_{NO} , $V_{NC} = 1.5 \text{ V}$, $R_L = 50 \Omega$, $C_L = 35 \text{ pF}$	Full		40	80		
Charge Injection ^d	Q _{INJ}	V+ = 2.7 V, C_L = 1 nF, R_{GEN} = 0 Ω , f = 500 kHz V_{NC} , V_{NO} = 2 V (test at COM side)	Room		- 25		рC	
Off-Isolation ^d	O _{IRR}	$V+=2.7~V,~C_L=1~nF,~R_{GEN}=0~\Omega,~f=500~kHz$ $V_{NC},~V_{NO}=2~V~(test~at~_{COM}~side)$	Room		- 90		40	
Crosstalk ^d	X _{TALK}	V+ = 2.7 V, C_L = 1 nF, R_{GEN} = 0 Ω V _{NC} , V_{NO} = 2 V (test at COM side)	Room		- 90		dB	
N N O# Canaditanad	C _{NO(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		35			
N _O , N _C Off Capacitance ^d	C _{NC(off)}		Room		35		pF	
Channel/On Capacitance ^d	C _{NO(on)}		Room		80			
	C _{NC(on)}	1	Room		80			
Power Supply		1				<u> </u>		
Power Supply Current	l+	V _{IN} = 0 or V+	Full			1	μA	

Notes:

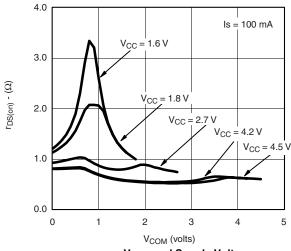
- a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.
- b. Typical values are for design aid only, not guaranteed nor subject to production testing.
- c. The algebraic convention where by the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- d. Guarantee by design, not subjected to production test.
- e. V_{IN} = input voltage to perform proper function.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

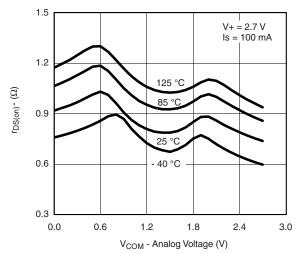
Vishay Siliconix

VISHAY.

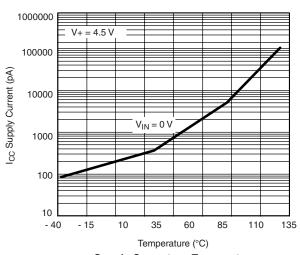
TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted



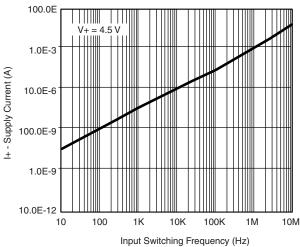
 $r_{\mbox{\scriptsize ON}}$ vs. $V_{\mbox{\scriptsize COM}}$ and Supply Voltage



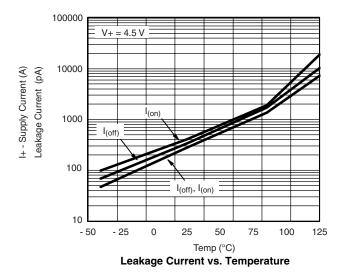
r_{ON} vs. Analog Voltage and Temperature



Supply Current vs. Temperature



Supply Current vs. Input Switching Frequency



2000 V+ = 4.5 V

1000 ICOM(on)

- 1000 INC(off), INO(off)

- 2000 0 1 2 3 4 5

V_{COM} - Analog Voltage (V)

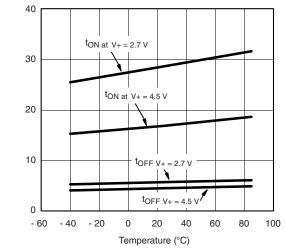
Leakage Current vs. Analog Voltage

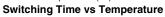


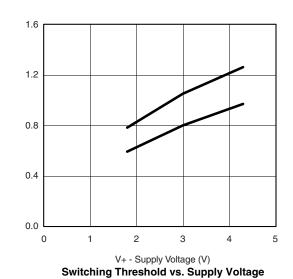
Time (ns)

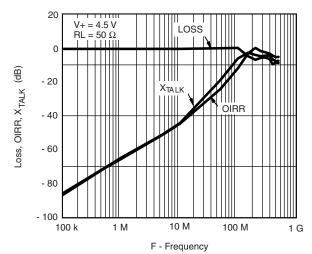
V_T - Switching Threshold (V)

TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted

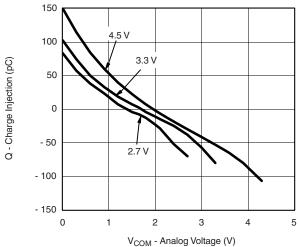








Insertion Loss, Off Isolation, Cross Talk vs. Frequency



Charge Injection vs. Analog Voltage

Vishay Siliconix

VISHAY.

TEST CIRCUITS

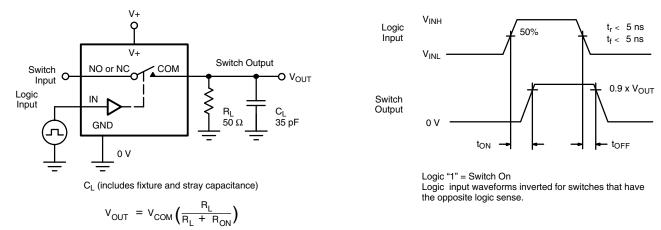


Figure 1. Switching Time

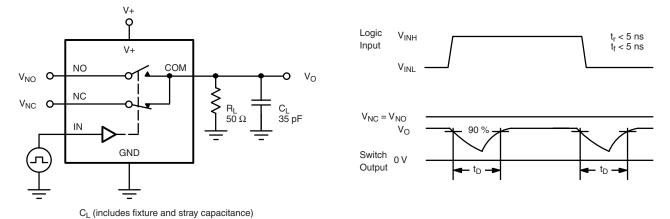


Figure 2. Break-Before-Make Interval

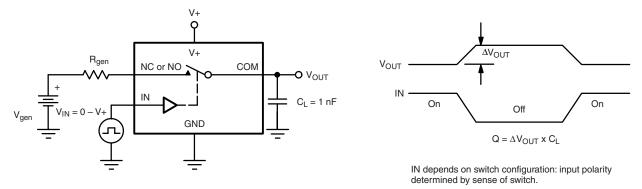


Figure 3. Charge Injection



TEST CIRCUITS

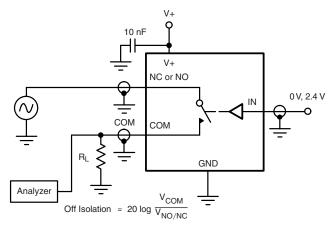


Figure 4. Off-Isolation

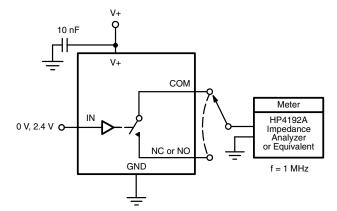


Figure 5. Channel Off/On Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?73482.



Vishay

Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.

Document Number: 91000 Revision: 18-Jul-08